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COMPLIANT

HALOGEN

FREE

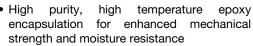
High Performance Schottky Rectifier, 8 A

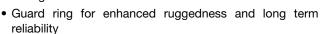


PRIMARY CHARACTERISTICS								
I _{F(AV)}	8 A							
V_{R}	80 V, 100 V							
V _F at I _F	0.58 V							
I _{RM}	7 mA at 125 °C							
T_J max.	175 °C							
E _{AS}	7.5 mJ							
Package	D ² PAK (TO-263AB)							
Circuit configuration	Single							

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- · High frequency operation





- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

The VS-8TQ... Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I _{F(AV)}	Rectangular waveform	8	A					
V _{RRM}	Range	80/100	V					
I _{FSM}	t _p = 5 μs sine	850	A					
V _F	8 A _{pk} , T _J = 125 °C	0.58	V					
TJ	Range	-55 to +175	°C					

VOLTAGE RATINGS								
PARAMETER	SYMBOL	VS-8TQ080S-M3	VS-8TQ100S-M3	UNITS				
Maximum DC reverse voltage	V_{R}	80	100	V				
Maximum working peak reverse voltage	V_{RWM}	80	100	V				

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST COND	TEST CONDITIONS					
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at T _C = 157 °C	8	А				
Maximum peak one cycle		5 μs sine or 3 μs rect. pulse	Following any rated load	850				
non-repetitive surge current See fig. 7	I _{FSM}	10 ms sine or 6 ms rect. pulse	condition and with rated V _{RRM} applied	230	Α			
Non-repetitive avalanche energy	E _{AS}	T _J = 25 °C, I _{AS} = 0.50 A, L = 60 mH		7.50	mJ			
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T_J maximum $V_A = 1.5$ x V_R typical		0.50	А			



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ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST COI	VALUES	UNITS				
		8 A	T _J = 25 °C	0.72				
Maximum forward voltage drop	V _{FM} ⁽¹⁾	16 A	1j=25 C	0.88	V			
See fig. 1	VFM (1)	8 A	T _{.1} = 125 °C	0.58				
		16 A	1j = 123 O	0.69	1			
Maximum reverse leakage current	I _{RM} ⁽¹⁾	T _J = 25 °C	V_{R} = Rated V_{R}	0.55	mA			
See fig. 2	IRM (1)	T _J = 125 °C	v _R = nateu v _R	7				
Maximum junction capacitance	C _T	V _R = 5 V _{DC} (test signal range 100 kHz to 1 MHz), 25 °C		500	pF			
Typical series inductance	L _S	Measured lead to lead 5 m	8	nH				
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs				

Note

 $^{^{(1)}\,}$ Pulse width < 300 µs, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T _J , T _{Stg}		-55 to +175	°C			
Maximum thermal resistance, junction to case		R _{thJC}	DC operation See fig. 4	2.0	°C/W			
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.50				
Approximate weight				2	g			
Approximate weight				0.07	oz.			
Manustina taurus	minimum			6 (5)	kgf · cm			
Mounting torque	maximum			12 (10)	(lbf \cdot in)			
Marking device			Case style D ² PAK (TO-263AB)	8TQ0	080S			
			Case style D-PAR (10-203AB)	8TQ	8TQ100S			

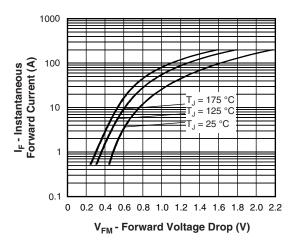


Fig. 1 - Maximum Forward Voltage Drop Characteristics

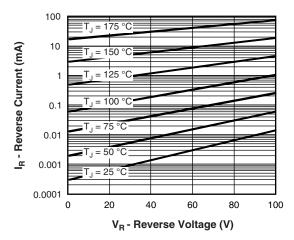


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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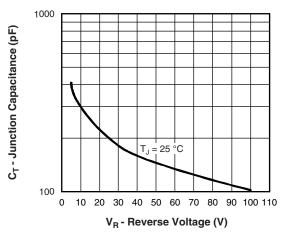


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

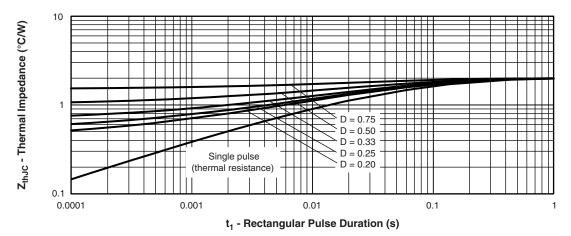


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

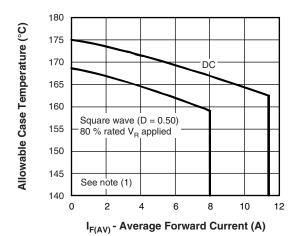


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

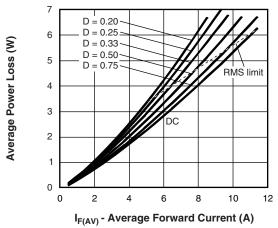
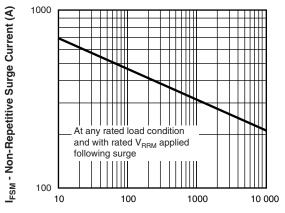


Fig. 6 - Forward Power Loss Characteristics

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t_p - Square Wave Pulse Duration (μs)

Fig. 7 - Maximum Non-Repetitive Surge Current

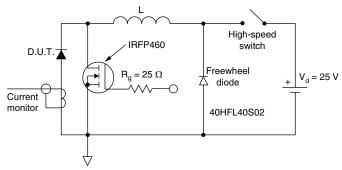
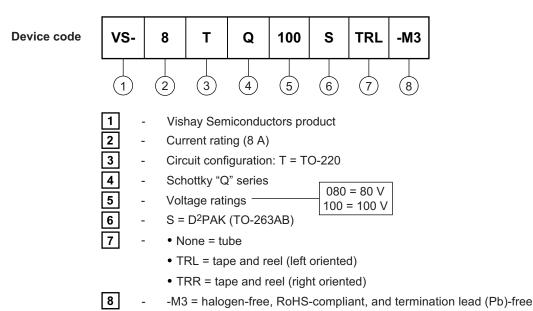


Fig. 8 - Unclamped Inductive Test Circuit

Note

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80 \%$ rated V_R

ORDERING INFORMATION TABLE





VS-8TQ080S-M3, VS-8TQ100S-M3

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ORDERING INFORMATION										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-8TQ080S-M3	50	1000	Antistatic plastic tubes							
VS-8TQ080STRR-M3	800	800	13" diameter reel							
VS-8TQ080STRL-M3	800	800	13" diameter reel							
VS-8TQ100S-M3	50	1000	Antistatic plastic tubes							
VS-8TQ100STRR-M3	800	800	13" diameter reel							
VS-8TQ100STRL-M3	800	800	13" diameter reel							

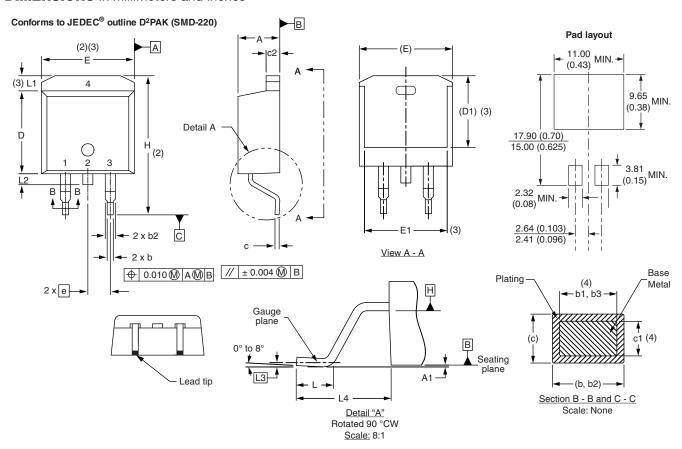
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96164					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					
SPICE model	www.vishay.com/doc?96227					



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES S	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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